

## **D/TEC-QCA Final Presentation Day - May 25<sup>th</sup>, 2005**

Co-60 TID Evaluation of SDRAMs from Elpida, EDS2508APTA 256Mbit, from Samsung, K4S510432B 512 Mbit and from Micron, MT48LC16M8A2 128Mbit, using Auto-refresh and Self-refresh mode of operation

- **ESTEC Contract No. 13528/99/NL/MV, COO-15**
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- Components tested

Manufacturer	Part Number	Description	TID Report
Elpida Memory Inc.	EDS2508APTA	SDRAM 8Mb x 8 x 4 , 133MHz	ESA_QCA0419T_C
Samsung	K4S510432B	SDRAM 32Mb x 4 x 4 , 133MHz	ESA_QCA0420T_C
Micron Technology Inc.	MT48LC16M8A2	SDRAM 4 Mb x 8 x 4 banks	ESA_QCA0421T_C

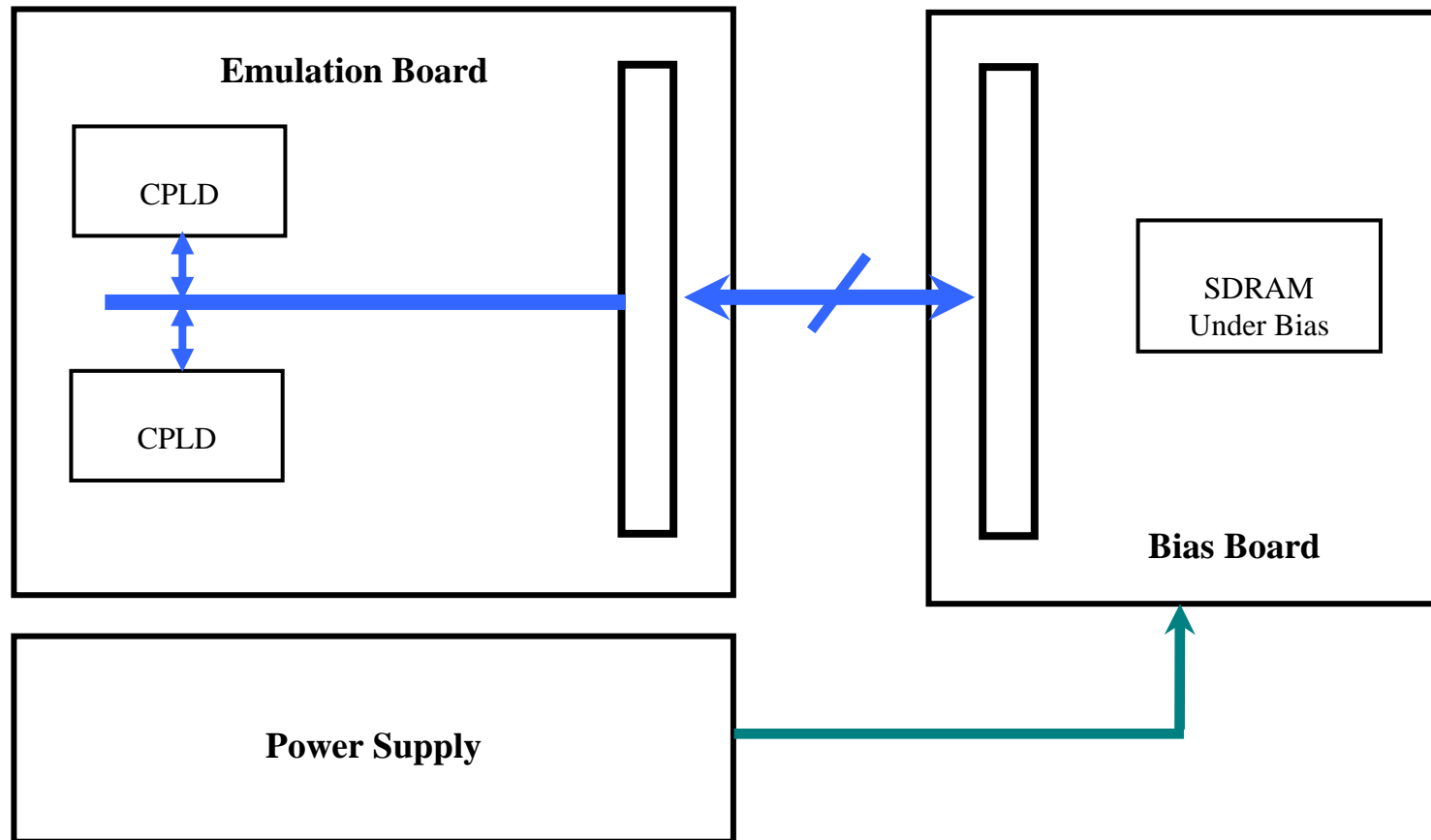
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- **Test conditions**

- Exposures: 9, 18, 32, 51, 69 & 98 Krad(Si) @ Room
- Dose rate: 200 Rad/hour
- Annealing: 24H @ Room + 168H @ 100°C under bias
- Bias conditions, 2 modes: Self-refresh & Auto-refresh
- Electrical parameters: Main static & Dynamic including functionality (4 patterns), timing parameters, Voh/Vol, Iih/Iil, Vih/Vil, Op. & standby Currents, Self & Auto refresh currents.

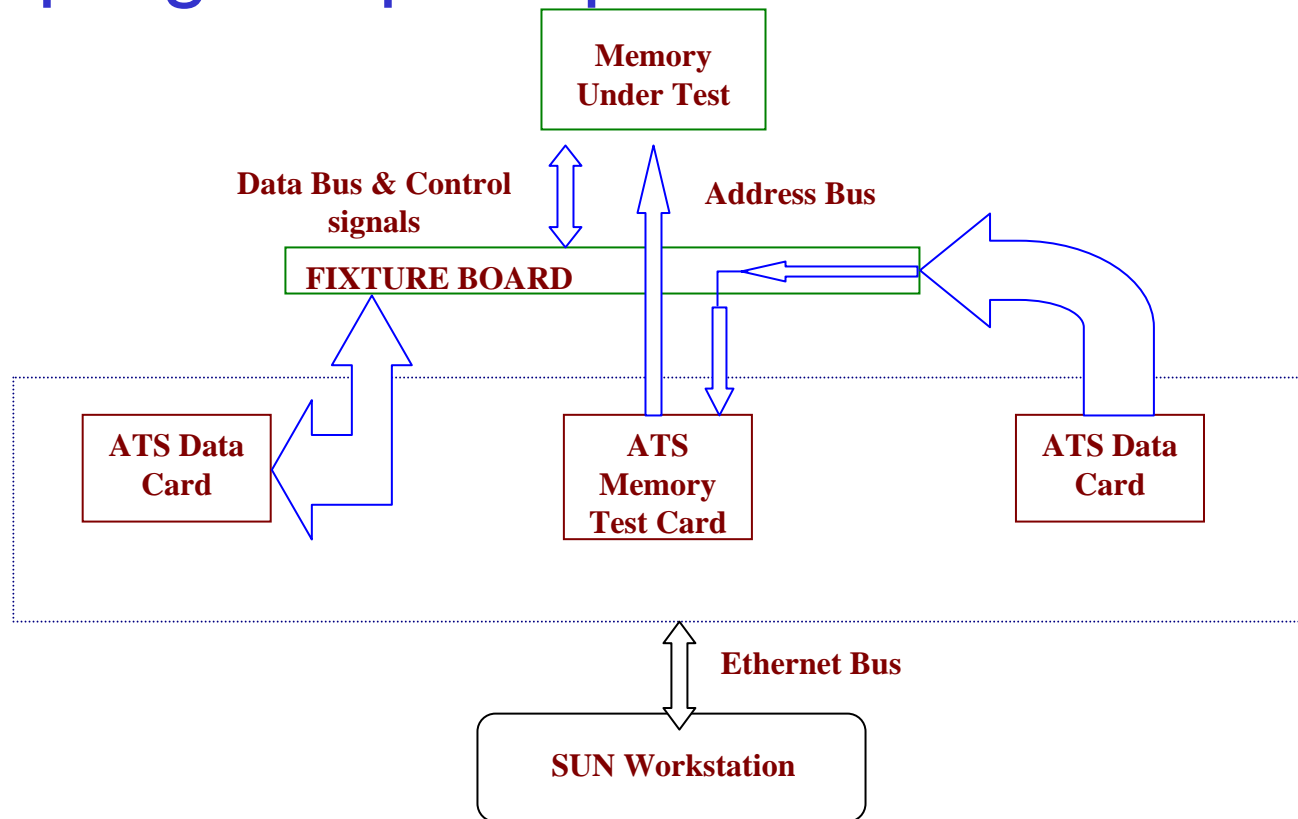
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- Bias conditions principle



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- Test program principle



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## • Test Results Elpida, EDS2508APTA

- All samples during irradiation exposures and annealing steps did not exhibit any failure.
- In particular none noticeable differences were recorded when considering the two different bias conditions used during exposures and annealing.

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## • Test Results Samsung, K4S510432B

- The most affected parameter was ICC6 the supply current in self refresh mode, that failed specification limits after 51 Krad(Si) of dose exposure. No recovery was observed after annealing.
- It should be noted that functionality of most samples were lost at 69 Krad(Si).
- Some of these samples have recovered their functionality after the last annealing step.
- No significant differences were noted between samples operating in self-refresh and auto-refresh modes during exposures and annealing.

Co-60 TID Evaluation of SDRAMs from Elpida, EDS2508APTA 256Mbit, from Samsung, K4S510432B 512 Mbit and from Micron, MT48LC16M8A2 128Mbit, using Auto-refresh and Self-refresh mode of operation

## • Test Results Micron, MT48LC16M8A2

- Generally this device exhibited a fairly good resistance to total dose induced effects. However, it should be noted that samples biased in self-refresh mode had a different behaviour than samples biased in auto-refresh mode.

\* Samples biased in self refresh mode :

- Lost of functionality after 98 KRad(Si). Recovery after annealing step.
- Parameters Idd1, Idd3, Idd4, Idd5, Idd6, Idd7, IozL, IozH, IiL (on pins CLK, CKE, /CS), IiH (on pins CLK, CKE, /CS) failed specification limits after 98 KRad(Si). Recovery after annealing step.

\*Samples biased in auto refresh mode :

- Samples passed specification limits for all parameters and remained functional all along testing.